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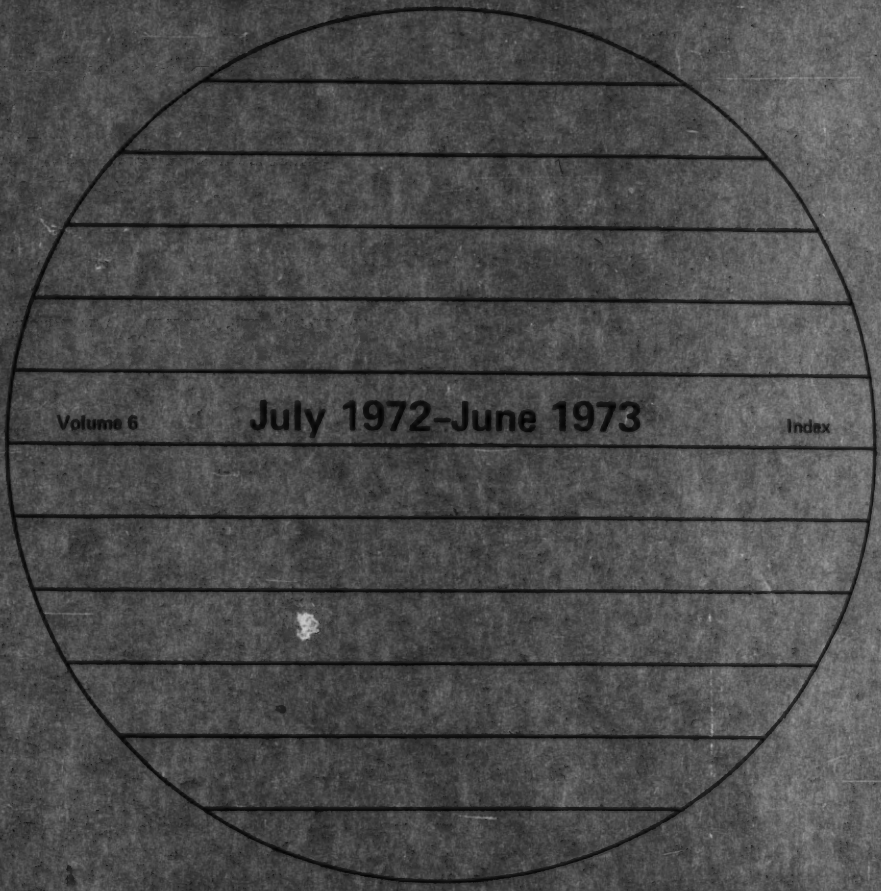

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5.10.40.90. Other Topics in Crystal Impurities

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5.15. LATTICE DYNAMICS

5.15.20. Phonons and Vibrations in Crystal Lattices

5.15.20.20. Phonon States, Bands, Normal Modes and Dispersion

Infrared Reflection Spectra of InP_xAs_{1-x} Solid Solutions (E)—N. P. Kekelidze, G. P. Kekelidze and Z. D. Makharadze. 6(6), 977–8(C) (Dec. 1972); CPM-7212D0636

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5.15.70. Surface and Interface Vibrations

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5.20. ENERGY STATES IN SOLIDS

5.20.20. Energy Band Structure and Fermi Surfaces of Specific Types of Materials

5.20.20.30. Semiconductors

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5.20.30.30. Semiconductors

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5.20.80.15. Forces and Interactions

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5.25. MECHANICAL AND ACOUSTICAL PHENOMENA

5.25.40. High-Pressure Effects in Solids

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5.30.40. Phase Properties of Systems

5.30.40.50. Solubility, Segregation and Mixing

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5.35.20. Carrier Properties

5.35.20.10. General

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5.35.20.30. Concentration, Density and Distribution

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5.35.30. Electronic Conduction in Metals and Alloys

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5.35.40. Electronic Conduction in Semiconductors and Insulators

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5.40.85.50. Domain Structure and Effects and Hysteresis

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5.55.20.40. Paramagnetic Resonance of Color Centers and Complex Centers

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5.60.20. Optical Constants of Materials and Optical Parameters

5.60.20.30. Optical Constants of Insulators

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5.60.60.30. Semiconductors

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5.60.70. Luminescence and Radiative Recombination in Solids

5.60.70.10. General Theory and Measurement Techniques

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5.70. PASSAGE OF PARTICLES AND RADIATION THROUGH SOLIDS

5.70.15. Radiowave and Microwave Interactions in Solids (Excluding Resonances)

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5.80.10. Structural Properties of Surfaces, Thin Films, Interfaces, Whiskers and Dendrites

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5.80.30.25. Semiconductors and Insulators

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5.80.40.15. Electronic and Thermal Transport

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5.90. SOLID STATE DEVICES

5.90.10. Detectors

5.90.10.10. Electromagnetic Radiation Detectors

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5.90.10.90. Other Detectors

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5.90.20.10. Junction and Barrier Photodevices

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5.90.20.30. Luminescent and Electroluminescent Devices

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5.90.20.40. Photoemission Devices

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5.90.70. Semiconductor Carrier Devices

5.90.70.10. Point Contact and Surface Barrier Diodes

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5.90.70.50. MIS, MOS Devices, etc.

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5.90.70.90. Other Semiconductor Carrier Devices

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5.90.80. Circuits and Circuit Elements

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6.30. OPTICS

6.30.50. Lasers and Masers

6.30.50.40. Solid Lasers and Masers, Including Semiconducting and Glass

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